

Dual 4-Input NAND Gate

High-Performance Silicon-Gate CMOS

MC74AC20, MC74ACT20

Features

- Outputs Source/Sink 24 mA
- 'ACT20 Has TTL Compatible Inputs
- These are Pb-Free Devices

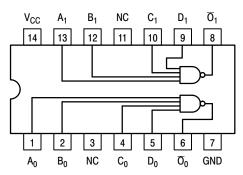


Figure 1. Pinout: 14-Lead Packages (Top View)

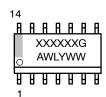
PIN ASSIGNMENT

PIN	FUNCTION
A _n , B _n , C _n , D _n	Inputs
Ō _n	Outputs

MARKING DIAGRAM



SOIC-14 D SUFFIX CASE 751A



XXXXXX = Specific Device Code A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week G or ■ = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5	V
VI	DC Input Voltage	$-0.5 \le V_{I} \le V_{CC} + 0.5$	V
Vo	DC Output Voltage (Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	±20	mA
I _{OK}	DC Output Diode Current	±50	mA
I _O	DC Output Sink/Source Current	±50	mA
I _{CC}	DC Supply Current per Output Pin	±50	mA
I _{GND}	DC Ground Current per Output Pin	±50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction temperature under Bias	+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	116	°C/W
P_{D}	Power Dissipation in Still Air at 25°C	1077	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 3) Charged Device Model (Note 4)	> 2000 > 1000	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 5)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I_O absolute maximum rating must be observed.
- 2. The package thermal impedance is calculated in accordance with JESD51-7.
- Tested to EIA/JESD22-A114-A.
 Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Min	Unit
	2 1 1 1	′AC	2.0	5.0	6.0	.,
V _{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V
VREG	DC Regulated Power Voltage (Ref. to GND)		0	-	V _{CC}	V
Input Rise and Fall Time (Note 1)	V _{CC} @ 3.0 V	-	150	-		
	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	-	ns/V
		V _{CC} @ 5.5 V	-	25	-	
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	-	10	-	0 /
t _r , t _f	'ACT Devices except Schmitt Inputs	V _{CC} @ 5.5 V	-	8.0	-	ns/V
T _A	Operating Ambient Temperature Range		-40	25	85	°C
I _{OH}	Output Current – HIGH		-	-	-24	mA
I _{OL}	Output Current – LOW		-	-	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. V_{in} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.

2. V_{in} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74	AC	74AC		
Symbol	Parameter V_{CC} $V_{A} = +25^{\circ}C$		+25°C	T _A = -40°C to +85°C	Unit	Conditions	
			Тур	Guar	anteed Limits		
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum Low Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	Ι _{ΟUT} = – 50 μΑ
		3.0 4.5 5.5		2.56 3.86 4.86	2.46 3.76 4.76	V	$\label{eq:VIN} \begin{split} *V_{IN} &= V_{IL} \text{ or } V_{IH} \\ &- 12 \text{ mA} \\ I_{OH} &- 24 \text{ mA} \\ &- 24 \text{ mA} \end{split}$
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	Ι _{ΟυΤ} = 50 μΑ
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	٧	$\begin{tabular}{ll} *V_{IN} = V_{IL} \mbox{ or } V_{IH} \\ 12 \mbox{ mA} \\ I_{OL} & 24 \mbox{ mA} \\ 24 \mbox{ mA} \\ \end{tabular}$
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	-75	mA	V _{OHD} = 3.85 V Min
Icc	Maximum Quiescent Supply Current	5.5	-	4.0	40	μΑ	V _{IN} = V _{CC} or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*All outputs loaded; thresholds on input associated with output under test.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V.

AC CHARACTERISTICS

			74AC			74AC		
Symbol Parameter		V _{CC} * (V)	T _A = +25°C C _L = 50 pF		T _A = -40°C to +85°C C _L = 50 pF		Unit	
			Min	Тур	Max	Min	Max	
t _{PLH}	Propagation Delay	3.3	2.0	6.0	8.5	1.5	10.0	ns
		5.0	1.5	5.0	7.0	1.0	8.0	115
t _{PHL}	Propagation Delay	3.3	1.5	5.0	7.0	1.0	9.0	
		5.0	1.5	4.0	6.0	1.0	7.0	ns

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. Voltage Range 5.0 V is 5.0 V ±0.5 V.

[†]Maximum test duration 2.0 ms, one output loaded at a time.

DC CHARACTERISTICS

			74	CT	74ACT		
Symbol	Parameter	V _{CC} (V)	T _A = +25°C		T _A = -40°C to +85°C	Unit	Conditions
			Тур	Guar	anteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = - 50 μA
		4.5 5.5	- -	3.86 4.86	3.76 4.76	V	$^{*V_{IN} = V_{IL} \text{ or } V_{IH}}_{I_{OH}} - ^{24} \text{ mA}$
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA
		4.5 5.5	- -	0.36 0.36	0.44 0.44	V	$\label{eq:VIN} \begin{array}{c} *V_{IN} = V_{IL} \text{ or } V_{IH} \\ 24 \text{ mA} \\ I_{OH} \\ 24 \text{ mA} \end{array}$
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	V _I = V _{CC} , GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	-	1.5	mA	V _I = V _{CC} – 2.1 V
I _{OLD}	†Minimum Dynamic	5.5	_	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	_	-	-75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	-	4.0	40	μΑ	V _{IN} = V _{CC} or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*All outputs loaded; thresholds on input associated with output under test.

AC CHARACTERISTICS

			74ACT			74ACT		
Symbol Parameter		V _{CC} * (V)		T _A = +25°C C _L = 50 pF		T _A = -40°C to +85°C C _L = 50 pF		Unit
			Min	Тур	Max	Min	Max	
t _{PLH}	Propagation Delay	5.0	2.0	6.5	9.0	1.5	10.5	ns
t _{PHL}	Propagation Delay	5.0	2.0	5.5	9.0	1.5	10.5	ns

^{*}Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	40	pF	V _{CC} = 5.0 V

[†]Maximum test duration 2.0 ms, one output loaded at a time.

ORDERING INFORMATION

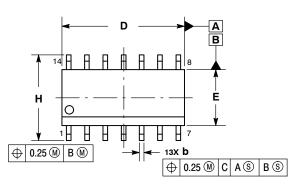
Device	Marking	Package	Shipping [†]
MC74AC20DG	AC20	SOIC-14 (Pb-Free)	55 Units/Rail
MC74AC20DR2G	AC20	SOIC-14 (Pb-Free)	2500/Tape & Reel
MC74ACT20DG	ACT20	SOIC-14 (Pb-Free)	55 Units/Rail
MC74ACT20DR2G	ACT20	SOIC-14 (Pb-Free)	2500/Tape & Reel

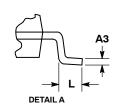


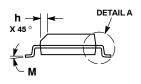


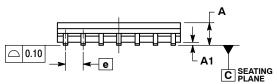
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









GENERIC MARKING DIAGRAM*

MIN MAX

0.050 BSC

0.068

0.019

0.054

0.25 0.004 0.010

0.25 0.008 0.010

0.50 0.010 0.019

1.25 0.016 0.049

0.49 0.014

8.55 8.75 0.337 0.344 3.80 4.00 0.150 0.157

NOTES:
1. DIMENSIONING AND TOLERANCING PER

5. MAXIMUM MOLD PROTRUSION 0.15 PER

MILLIMETERS MIN MAX

1.27 BSC

0.19

0.25

0.40

SIDE

Α

A1 0.10

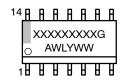
АЗ

b 0.35

D 8.55 E 3.80

e H h

ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS.
DIMENSION b DOES NOT INCLUDE DAMBAR
PROTRUSION. ALLOWABLE PROTRUSION
SHALL BE 0.13 TOTAL IN EXCESS OF AT
MAXIMUM MATERIAL CONDITION.
DIMENSIONS D AND E DO NOT INCLUDE
MOLD PROTRUSIONS.



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DIMENSIONS: MILLIMETERS

STYLES ON PAGE 2

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SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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